In the claims:



1. (Currently amended) A method of fabricating SWNT probes for use in atomic force microscopy, consisting emprising the steps of:

growing SWNTs on a substrate using chemical vapor deposition; imaging said substrate using an atomic force microscope comprising a tip; and attaching one of said SWNTs to said tip, thereby producing a tip bearing a

SWNT.

- 2. (Original) The method of claim 1 wherein the SWNTs are deposited normal to the surface of said substrate.
- 3. (Original) The method of claim 2 wherein the substrate is a silicon wafer.
- 4. (Original) The method of claim 3 wherein growing the SWNTs on a silicon wafer comprises the steps of:

depositing on said wafer a metallic catalytic material;

placing said silicon wafer in a CVD furnace; and

exposing said silicon wafers to a gaseous atmosphere comprising a carbon containing gas.

- 5. (Original) The method of claim 4 wherein the metallic catalytic material is selected from the group consisting of metals, metal oxides, metallic salts, and metallic particles.
- 6. (Original) The method of claim 4 wherein the metallic catalytic material is in solution.
- 7. (Original) The method of claim 6 wherein the metallic catalytic material is selected from the group consisting of ferric salts, nickel salts, cobalt salts, platinum salts, molybdenum salts, and ruthenium salts.
- 8. (Original)The method of claim 7 wherein the metallic catalytic material is ferric nitrate.
- 9. (Original)The method of claim 6 wherein the solution comprises an alcohol.
- 10. (Original) The method of claim 9 wherein the alcohol is selected from the group consisting of methanol, ethanol, and isopropanol.

- 11. (Original) The method of claim 10 wherein the alcohol is isopropanol.
- 12. (Original) The method of claim 4 wherein the carbon containing gas is ethylene.
- 13. (Original) The method of claim 9 wherein the carbon containing gas is ethylene, the metallic catalytic material is ferric nitrate, and the alcohol is isopropanol.
- 14. (Canceled)
- 15. (Original) The method of claim 3 wherein growing the SWNTs on a silicon wafer comprises the steps of:

treating said silicon wafer with metallic colloid particles;
placing said silicon wafer in a CVD furnace; and
exposing said silicon wafers to a gaseous atmosphere comprising a carbon
containing gas.

- 16. (Original) The method of claim 15 wherein the metallic colloid is selected from the group consisting of iron colloids, nickel colloids, cobalt colloids, platinum colloids, molybdenum colloids, and ruthenium colloids.
- 17. (Original) The method of claim 16 wherein the metallic colloid is an iron colloid.
- 18. (Original) The method of claim 15 wherein the carbon containing gas is ethylene.
- 19. (Original) The method of claim 15 wherein the metallic colloids have diameters of about 3-15 nm.
- 20. (Original) The method of claim 1 wherein the SWNT has a diameter from about 2 nm to about 13 nm.
- 21. (Original) The method of claim 1 wherein the SWNT has a diameter from about 2 nm to about 9 nm.
- 22. (Original) The method of claim 1 wherein the SWNT has a diameter from about 3 nm to about 5 nm.
- 23. (Original) The method of claim 1 wherein said tip bears an adhesive.
- 24. (Currently amended) A The method of fabricating a SWNT probe for use in atomic force microscopy, comprising:

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growing SWNTs on a substrate using chemical vapor deposition;

imaging said substrate using an atomic force microscope comprising a tip;

attaching one of said SWNTs to said tip thereby producing a tip bearing a SWNT;

and

further comprising the step of heating said tip bearing a SWNT to 900 °C; thereby

fabricating the SWNT probe.

25. (Canceled)

26. (Withdrawn) A method of growing carbon nanotubes comprising the steps of: providing a substrate;

treating said substrate with a metallic colloid solution;

placing said substrate in a CVD furnace; and

exposing said substrate to a gaseous atmosphere comprising a carbon containing gas, thereby growing a carbon nanotube on said substrate.

- 27. (Withdrawn) The method of claim 26, wherein said carbon nanotube is a SWNT.
- 28. (Withdrawn) The method of claim 26, wherein said carbon nanotube is a MWNT.
- 29. (Withdrawn) The method of claim 26, wherein said substrate is a silicon wafer.
- 30. (Withdrawn) The method of claim 26 wherein the metallic colloid is selected from the group consisting of iron colloids, nickel colloids, cobalt colloids, platinum colloids, molybdenum colloids and ruthenium colloids.
- 31. (Withdrawn) The method of claim 30 wherein the metallic colloid is an iron colloid.
- 32. (Withdrawn) The method of claim 26 wherein the carbon containing gas is ethylene.
- 33. (Withdrawn) The method of claim 31 wherein the carbon containing gas is ethylene.
- 34. (Withdrawn) The method of claim 26 wherein the metallic colloids have diameters of about 3-15 nm.
- 35. (Withdrawn) The method of claim 26 wherein the solution comprises an organic solvent.
- 36. (Withdrawn) The method of claim 35 wherein the solution comprises toluene.